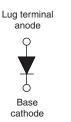
Vishay Semiconductors

High Performance Schottky Rectifier, 120 A



www.vishay.com

HALF-PAK (D-67)



| PRIMARY CHARACTERISTICS | | | | |
|------------------------------------|-----------------|--|--|--|
| I _{F(AV)} 120 A | | | | |
| V _R | 45 V | | | |
| Package | HALF-PAK (D-67) | | | |
| Circuit configuration Single diode | | | | |

FEATURES

- 175 °C T_J operation
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- · Designed and qualified for industrial level
- UL approved file E222165
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

The VS-121NQ.. high current Schottky rectifier module series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in high current switching power supplies, plating power supplies, UPS systems, converters, freewheeling diodes, welding, and reverse battery protection.

| MAJOR RATINGS AND CHARACTERISTICS | | | | | | |
|-----------------------------------|---|-------------|----|--|--|--|
| SYMBOL | CHARACTERISTICS VALUES UNITS | | | | | |
| I _{F(AV)} | Rectangular waveform | 120 | A | | | |
| V _{RRM} | | 45 | V | | | |
| I _{FSM} | t _p = 5 μs sine | 16 000 | A | | | |
| V _F | 120 A _{pk} , T _J = 125 °C | 0.6 | V | | | |
| TJ | Range | -55 to +175 | °C | | | |

| VOLTAGE RATINGS | | | | | | |
|--------------------------------------|------------------|----------------|-------|--|--|--|
| PARAMETER | SYMBOL | VS-121NQ045PbF | UNITS | | | |
| Maximum DC reverse voltage | V _R | 45 | V | | | |
| Maximum working peak reverse voltage | V _{RWM} | 40 | v | | | |

| ABSOLUTE MAXIMUM RATINGS | | | | | | |
|--|--------------------|---|--------|--------|----|--|
| PARAMETER | SYMBOL | TEST CONDI | VALUES | UNITS | | |
| Maximum average forward current See fig. 5 | I _{F(AV)} | 50 % duty cycle at T_C = 137 °C, | 120 | A | | |
| Maximum peak one cycle non-repetitive surge current | I | 5 µs sine or 3 µs rect. pulse Following any rated load condition and with rated | | 16 000 | А | |
| See fig. 7 | IFSM | 10 ms sine or 6 ms rect. pulse | | | ~ | |
| Non-repetitive avalanche energy | E _{AS} | T _J = 25 °C, I _{AS} = 13 A, L = 1 mH | | 81 | mJ | |
| Repetitive avalanche current | I _{AR} | Current decaying linearly to zero in 1 μ s Frequency limited by T _J maximum V _A = 1.5 x V _R typical | | 13 | А | |

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| ELECTRICAL SPECIFICATIONS | | | | | | |
|---------------------------------|--------------------------------|---|---------------------------------|-------|----|--|
| PARAMETER | SYMBOL | TEST CO | VALUES | UNITS | | |
| | | 120 A | T _{.1} = 25 °C | 0.65 | | |
| Maximum forward voltage drop | V _{FM} ⁽¹⁾ | 240 A | 1j=25 C | 0.82 | V | |
| See fig. 1 | VFM (') | 120 A | T.I = 125 °C | 0.6 | | |
| | | 240 A | 1j = 125 C | 0.76 | | |
| Maximum reverse leakage current | | $T_J = 25 \ ^{\circ}C$ | $V_{\rm B}$ = Rated $V_{\rm B}$ | 10 | | |
| See fig. 2 | I _{RM} | T _J = 125 °C | $v_{\rm R} = naleu v_{\rm R}$ | 90 | mA | |
| Maximum junction capacitance | CT | V _R = 5 V _{DC} (test signal ran | 5200 | pF | | |
| Typical series inductance | L _S | From top of terminal hole | 7.0 | nH | | |
| Maximum voltage rate of change | dV/dt | Rated V _R | 10 000 | V/µs | | |

Note

⁽¹⁾ Pulse width = 500 μ s

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|--|--------------------|-----------------------------------|--------------------------------------|------------|---------------------|--|
| PARAMETER | | SYMBOL | SYMBOL TEST CONDITIONS | | UNITS | |
| Maximum junction and storage te | mperature range | T _J , T _{Stg} | | -55 to 175 | °C | |
| Maximum thermal resistance, junction to case | | R _{thJC} | DC operation See fig. 4 | 0.38 | °C/W | |
| Typical thermal resistance, case to heatsink | | R _{thCS} | Mounting surface, smooth and greased | 0.05 | | |
| Approvimete weight | | | | 30 | g | |
| Approximate weight | Approximate weight | | | 1.06 | oz. | |
| Mounting torque minimum maximum | | | | 3 (26.5) | N ⋅ m (lbf ⋅ in) | |
| | | | Non-lubricated threads | 4 (35.4) | | |
| Terminal torque minimum maximum | | | Non-Iudricated trireads | 3.4 (30) | | |
| | | | | 5 (44.2) | | |
| Case style | | | | HALF-PA | K module | |

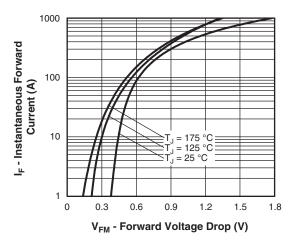
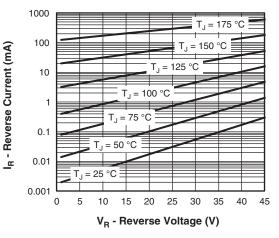
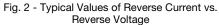


Fig. 1 - Maximum Forward Voltage Drop Characteristics





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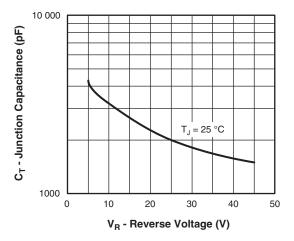


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

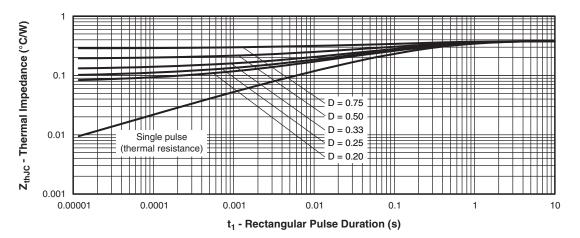
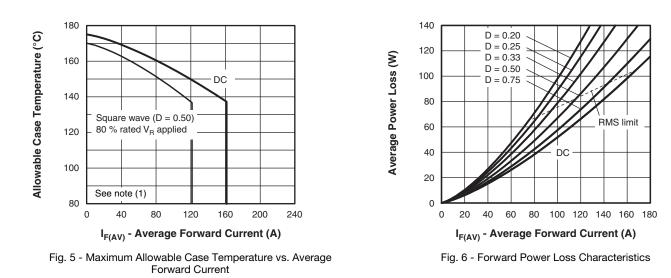


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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VS-121NQ045PbF

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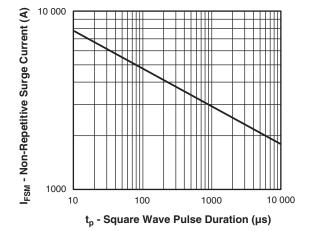


Fig. 7 - Maximum Non-Repetitive Surge Current

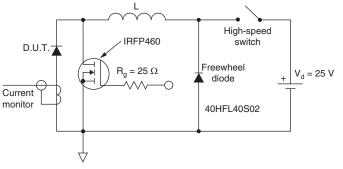


Fig. 8 - Unclamped Inductive Test Circuit

Note

- $\begin{array}{ll} \mbox{(1)} & \mbox{Formula used: } T_C = T_J (Pd + Pd_{REV}) \ x \ R_{thJC}; \\ Pd = \mbox{forward power loss} = I_{F(AV)} \ x \ V_{FM} \ at \ (I_{F(AV)}/D) \ (see \ fig. \ 6); \\ Pd_{REV} = \ \mbox{inverse power loss} = V_{R1} \ x \ I_R \ (1 D); \ I_R \ at \ V_{R1} = \ rated \ V_R \end{array}$

ORDERING INFORMATION TABLE

| Device code | VS- | 12 | 1 | Ν | Q | 045 | PbF |
|-------------|------------------------------------|------|----------|----------|-----------|-------|-----|
| | 1 | 2 | 3 | 4 | 5 | 6 | 7 |
| | 1 - | Visl | nay Sem | niconduc | ctors pro | oduct | |
| | 2 - Average current rating (x 10) | | | | | | |
| | 3 - Product silicon identification | | | | | | |
| | 4 - N = not isolated | | | | | | |
| | 5 - Q = Schottky rectifier diode | | | | | | |
| | 6 - Voltage rating (045 = 45 V) | | | | | | |
| | 7 - | Lea | d (Pb)-f | ree | | | |

| LINKS TO RELATED DOCUMENTS | | | | |
|---|---|------------------------|--|--|
| Dimensions www.vishay.com/doc?95020 | | | | |
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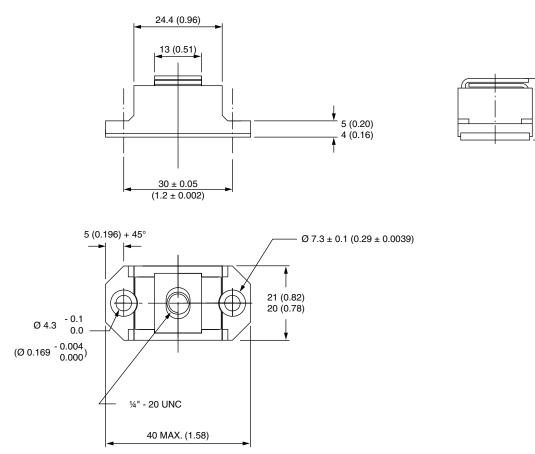
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17.5 (0.69) 16.5 (0.65)



DIMENSIONS in millimeters (inches)

SHAY





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